

B¹ Sub
D¹

1 24. (Twice Amended) A poly-poly capacitor ^{over a substrate} comprising upper and lower plate electrodes, wherein at least the upper plate electrode is composed of SiGe polysilicon, said plate electrodes being separated by an insulator structure and said upper plate electrode is located directly above said insulator structure and said lower plate electrode is located directly below said insulator structure, ~~and between the insulator structure and the substrate.~~

B² Sub
D¹

5 26. (Twice Amended) A poly-poly capacitor comprising upper and lower plate electrodes, wherein the upper plate electrode and the lower plate electrode are both composed of SiGe polysilicon, said plate electrodes being separated by an insulator structure.

B³ Sub
D¹

7 30. (Amended) A semiconductor structure, comprising
a first layer of polysilicon patterned to form a first electrode of a MOS device and a first plate electrode of a capacitor, and
a second layer of polysilicon patterned to form a first electrode of a bipolar device and a second plate electrode of said capacitor, said second layer being comprised of SiGe polysilicon.

REMARKS

Favorable reconsideration of this application in view of the foregoing amendments and remarks to follow is respectfully requested. Since the present amendment raises no new issues and, in any event, places the application in better condition for consideration on appeal, entry thereof is respectfully requested.

Before addressing the specific grounds of objection/rejection raised in the present Office Action, applicants acknowledge the Examiner's indication that Claim 29 is allowable over the art of the record. Applicants also note that the Examiner has indicated that Claims 26